

N-Channel Power MOSFET

30V, 78A, 3.8mΩ

FEATURES

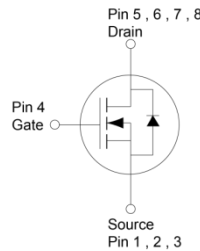
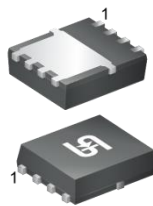
- Low $R_{DS(ON)}$ to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS

PARAMETER		VALUE	UNIT
V_{DS}		30	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	3.8	mΩ
	$V_{GS} = 4.5V$	5.5	
Q_g		24	nC

APPLICATIONS

- DC-DC Converters
- Battery Power Management
- ORing FET/Load Switching


PDFN33


Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (Note 1)	$T_C = 25^\circ\text{C}$	I_D	78	A
	$T_A = 25^\circ\text{C}$		19	
Pulsed Drain Current		I_{DM}	312	A
Single Pulse Avalanche Current (Note 2)		I_{AS}	26	A
Single Pulse Avalanche Energy (Note 2)		E_{AS}	101	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	39	W
	$T_C = 125^\circ\text{C}$		7.8	
Total Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	2.4	W
	$T_A = 125^\circ\text{C}$		0.5	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	3.2	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	53	$^\circ\text{C/W}$

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	BV _{DSS}	30	--	--	V
Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250μA	V _{GS(TH)}	1.2	1.6	2.5	V
Gate-Source Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Drain-Source Leakage Current	V _{GS} = 0V, V _{DS} = 30V	I _{DSS}	--	--	1	μA
	V _{GS} = 0V, V _{DS} = 30V T _J = 125°C		--	--	100	
Drain-Source On-State Resistance (Note 3)	V _{GS} = 10V, I _D = 19A	R _{DS(on)}	--	3	3.8	mΩ
	V _{GS} = 4.5V, I _D = 16A		--	4	5.5	
Forward Transconductance (Note 3)	V _{DS} = 5V, I _D = 19A	g _{fs}	--	48	--	S
Dynamic (Note 4)						
Total Gate Charge	V _{GS} = 10V, V _{DS} = 15V, I _D = 19A	Q _g	--	48	--	nC
Total Gate Charge	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 16A	Q _g	--	24	--	
Gate-Source Charge		Q _{gs}	--	6.9	--	
Gate-Drain Charge		Q _{gd}	--	11	--	
Input Capacitance	V _{GS} = 0V, V _{DS} = 15V f = 1.0MHz	C _{iss}	--	2557	--	pF
Output Capacitance		C _{oss}	--	380	--	
Reverse Transfer Capacitance		C _{rss}	--	276	--	
Gate Resistance	f = 1.0MHz	R _g	0.5	1.5	3	Ω
Switching (Note 4)						
Turn-On Delay Time	V _{GS} = 10V, V _{DS} = 15V, I _D = 19A, R _G = 2Ω,	t _{d(on)}	--	11	--	ns
Turn-On Rise Time		t _r	--	80	--	
Turn-Off Delay Time		t _{d(off)}	--	33	--	
Turn-Off Fall Time		t _f	--	65	--	
Source-Drain Diode						
Forward Voltage (Note 3)	V _{GS} = 0V, I _S = 19A	V _{SD}	--	--	1	V
Reverse Recovery Time	I _S = 19A , dI/dt = 100A/μs	t _{rr}	--	33	--	ns
Reverse Recovery Charge		Q _{rr}	--	19	--	nC

Notes:

1. Silicon limited current only.
2. $L = 0.3\text{mH}$, $V_{GS} = 10V$, $V_{DD} = 25V$, $R_G = 25\Omega$, $I_{AS} = 26A$, Starting $T_J = 25^\circ\text{C}$
3. Pulse test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Switching time is essentially independent of operating temperature.

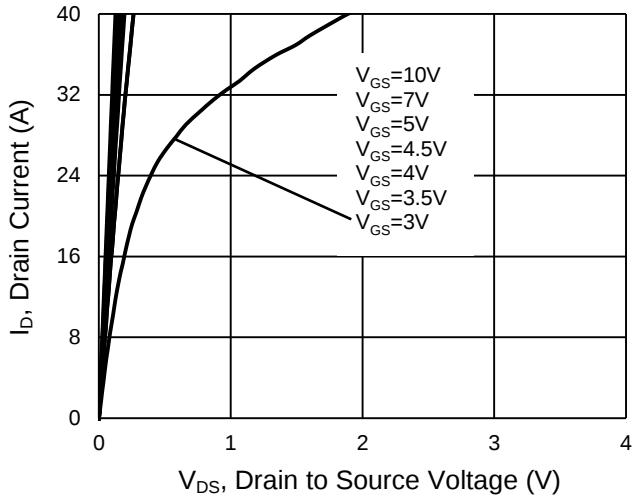
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM038N03PQ33 RGG	PDFN33	5,000pcs / 13" Reel

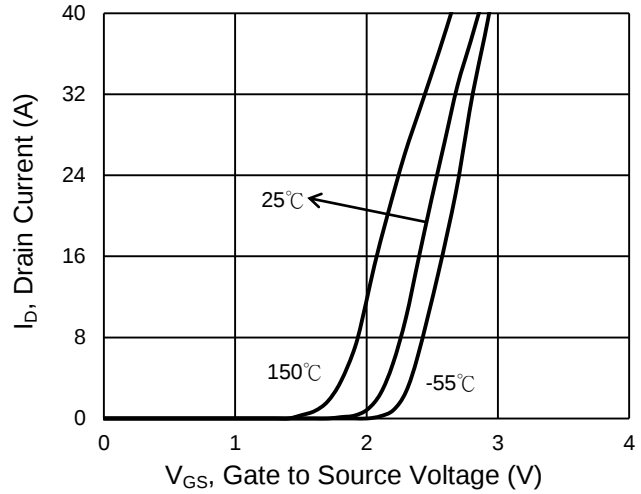
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

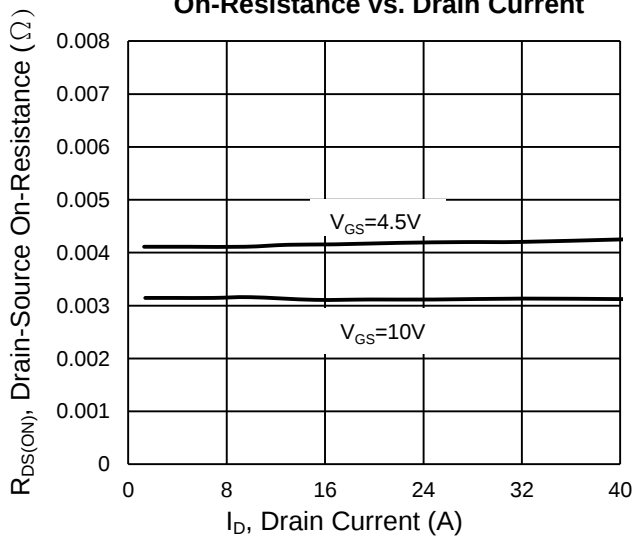
Output Characteristics



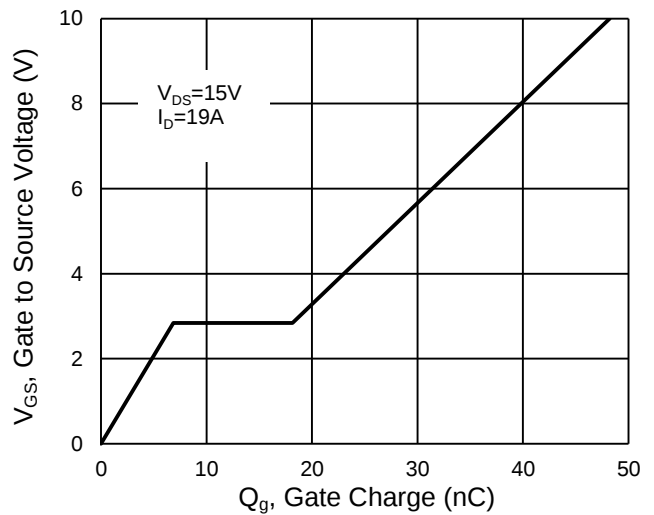
Transfer Characteristics



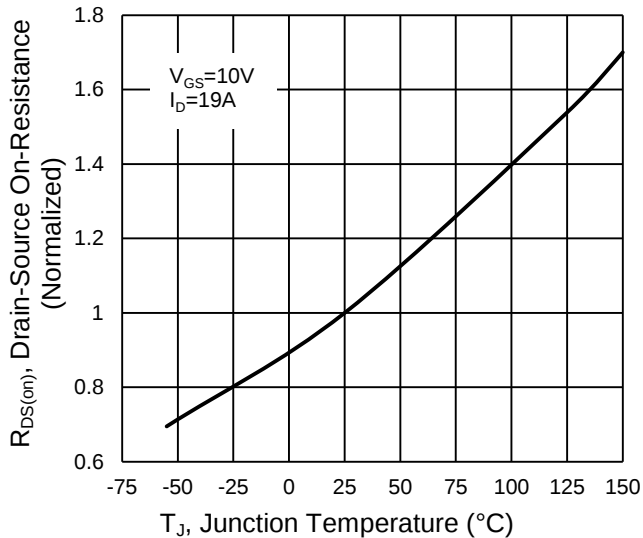
On-Resistance vs. Drain Current



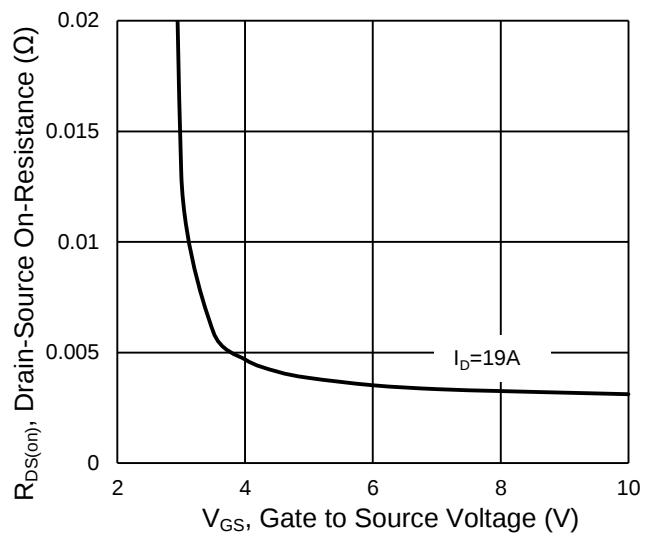
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



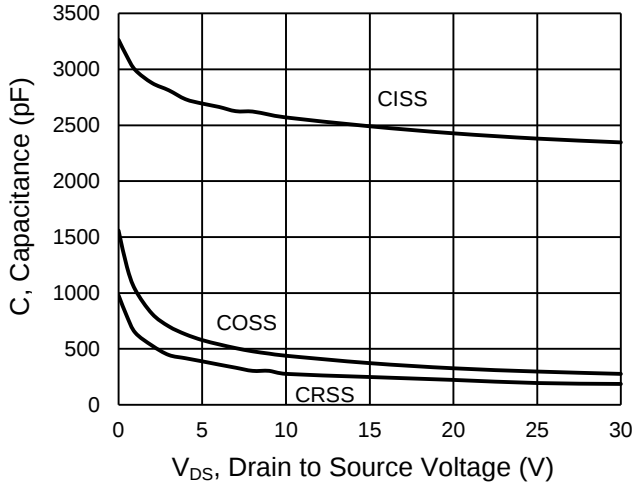
On-Resistance vs. Gate-Source Voltage



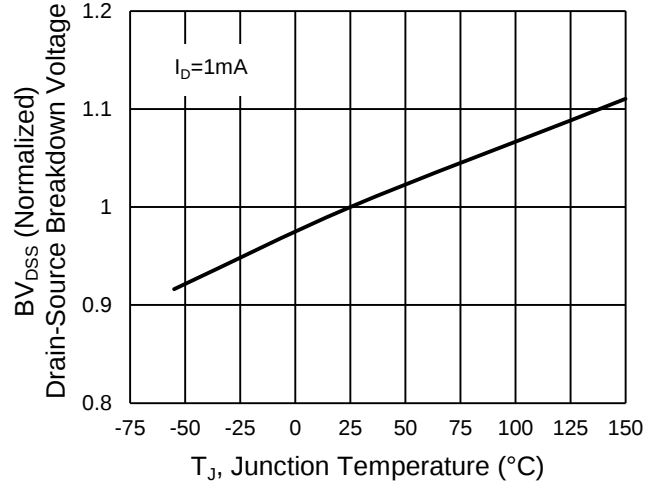
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

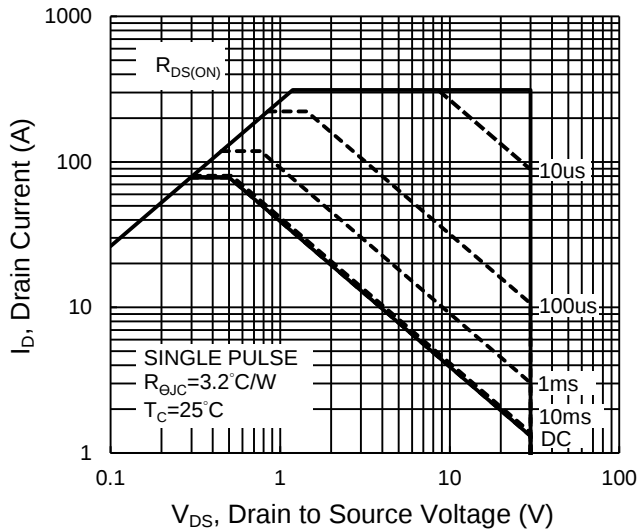
Capacitance vs. Drain-Source Voltage



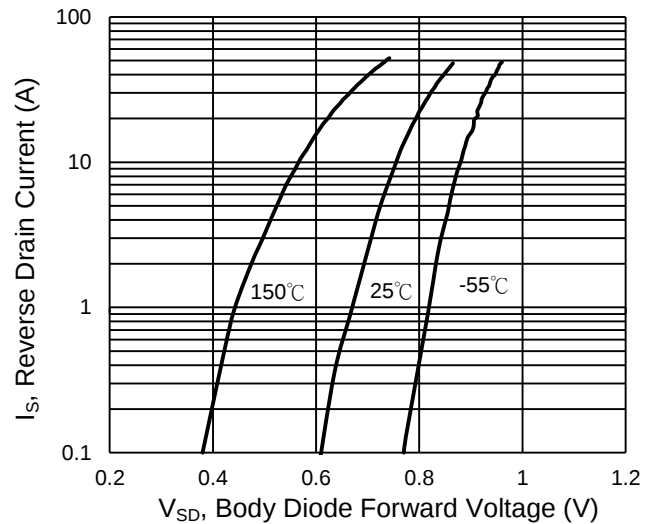
BV_{DSS} vs. Junction Temperature



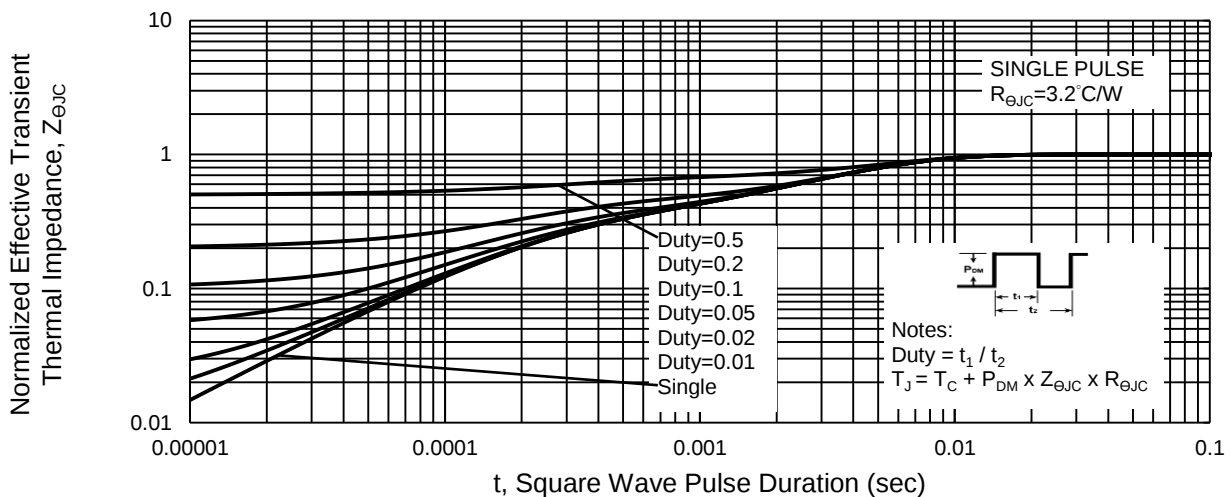
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

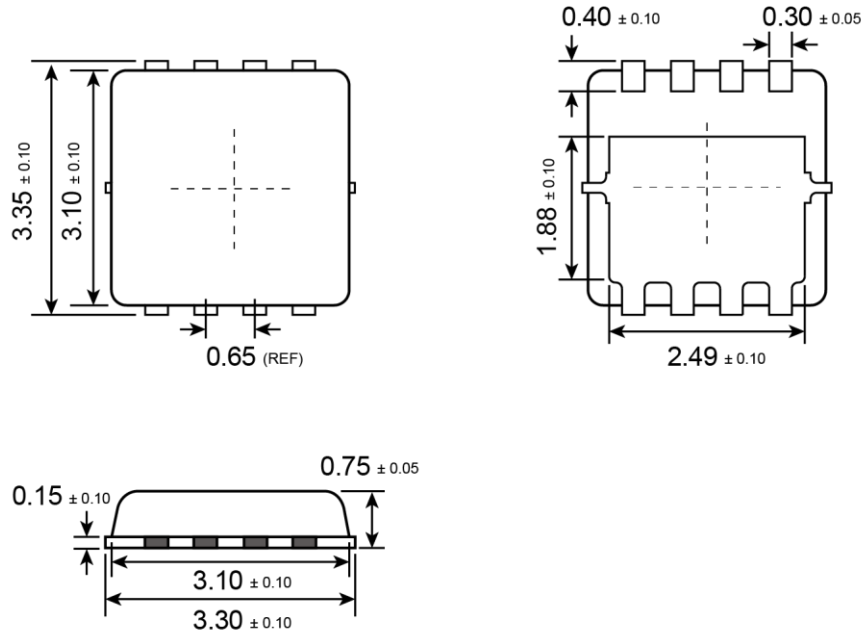


Normalized Thermal Transient Impedance, Junction-to-Case

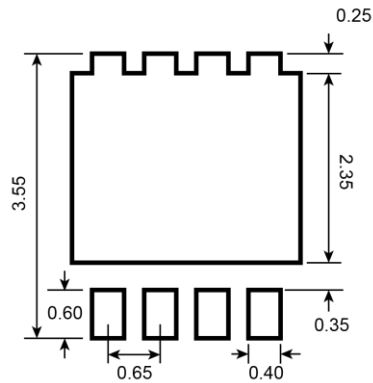


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

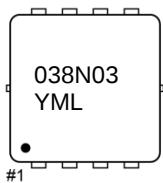
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SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code

O =Jan **P** =Feb **Q** =Mar **R** =Apr

S =May **T** =Jun **U** =Jul **V** =Aug

W =Sep **X** =Oct **Y** =Nov **Z** =Dec

L = Lot Code (1~9, A~Z)

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